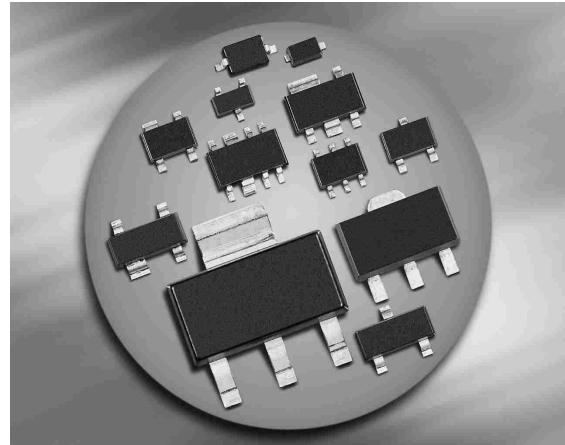
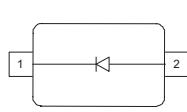


Silicon PIN Diode

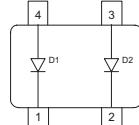
- Optimized for low current antenna switches in hand held applications
- Very low forward resistance (typ. 1.5Ω @ $I_F = 1 \text{ mA}$)
- Low capacitance at zero volt reverse bias at frequencies above 1 GHz (typ. 0.28 pF)
- Very low signal distortion



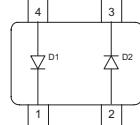
**BAR88-02L
BAR88-02V**



BAR88-07L4



BAR88-099L4



Type	Package	Configuration	$L_S(\text{nH})$	Marking
BAR88-02L	TSLP-2-1	single, leadless	0.4	UU
BAR88-02V	SC79	single	0.6	U
BAR88-07L4*	TSLP-4-4	parallel pair, leadless	0.4	UT
BAR88-099L4*	TSLP-4-4	anti-parallel pair, leadless	0.4	US

* Preliminary Data

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Forward current	I_F	100	mA
Total power dissipation BAR88-02L, -07L4, -099L4 $T_s \leq 133^\circ\text{C}$	P_{tot}	250	mW
$T_s \leq 123^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BAR88-02L, 07L4, -099L4	R_{thJS}	≤ 65	K/W
BAR88-02V		≤ 105	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Breakdown voltage $I_{(BR)} = 5 \mu\text{A}$	$V_{(BR)}$	80	-	-	V
Reverse current $V_R = 60 \text{ V}$	I_R	-	-	50	nA
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 100 \text{ mA}$	V_F	-	0.75 0.95	0.9 1.2	V

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

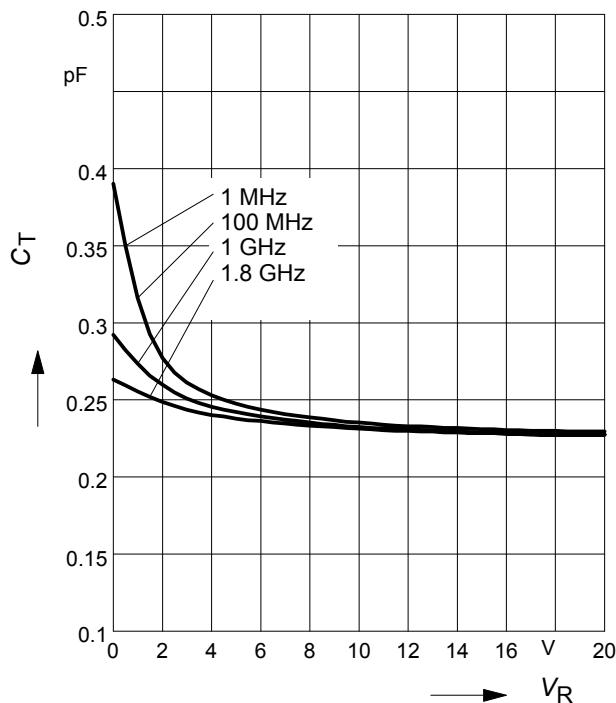
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 1 \text{ V}, f = 1 \text{ MHz}$	C_T	-	0.3	0.4	pF
$V_R = 0 \text{ V}, f = 100 \text{ MHz}$		-	0.4	-	
$V_R = 0 \text{ V}, f = 1 \text{ GHz}$		-	0.28	-	
$V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	0.25	-	
Reverse parallel resistance $V_R = 0 \text{ V}, f = 100 \text{ MHz}$	R_P	-	65	-	kΩ
$V_R = 0 \text{ V}, f = 1 \text{ GHz}$		-	2.5	-	
$V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	1.5	-	
Forward resistance $I_F = 1 \text{ mA}, f = 100 \text{ MHz}$	r_f	-	1.5	2.5	Ω
$I_F = 5 \text{ mA}, f = 100 \text{ MHz}$		-	0.8	-	
$I_F = 10 \text{ mA}, f = 100 \text{ MHz}$		-	0.6	-	
Charge carrier life time $I_F = 10 \text{ mA}, I_R = 6 \text{ mA}, \text{ measured at } I_R = 3 \text{ mA}, R_L = 100 \Omega$	τ_{rr}	-	500	-	ns
I-region width	W_I	-	13	-	μm
Insertion loss ¹⁾ $I_F = 1 \text{ mA}, f = 1.8 \text{ GHz}$	$ S_{21} ^2$	-	-0.11	-	dB
$I_F = 5 \text{ mA}, f = 1.8 \text{ GHz}$		-	-0.07	-	
$I_F = 10 \text{ mA}, f = 1.8 \text{ GHz}$		-	-0.06	-	
Isolation ¹⁾ $V_R = 0 \text{ V}, f = 0.9 \text{ GHz}$	$ S_{21} ^2$	-	-15	-	
$V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	-11	-	
$V_R = 0 \text{ V}, f = 2.45 \text{ GHz}$		-	-9	-	

¹BAR88-02L in series configuration, $Z = 50\Omega$

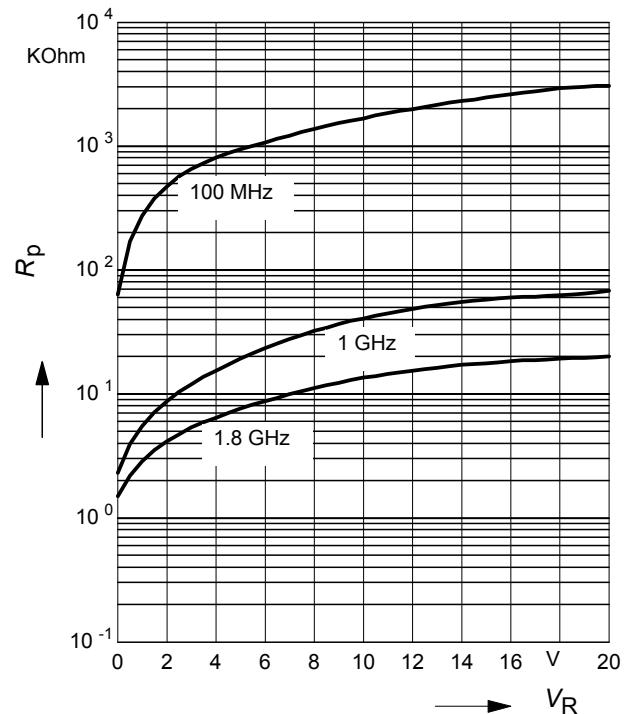
Diode capacitance $C_T = f(V_R)$

f = Parameter



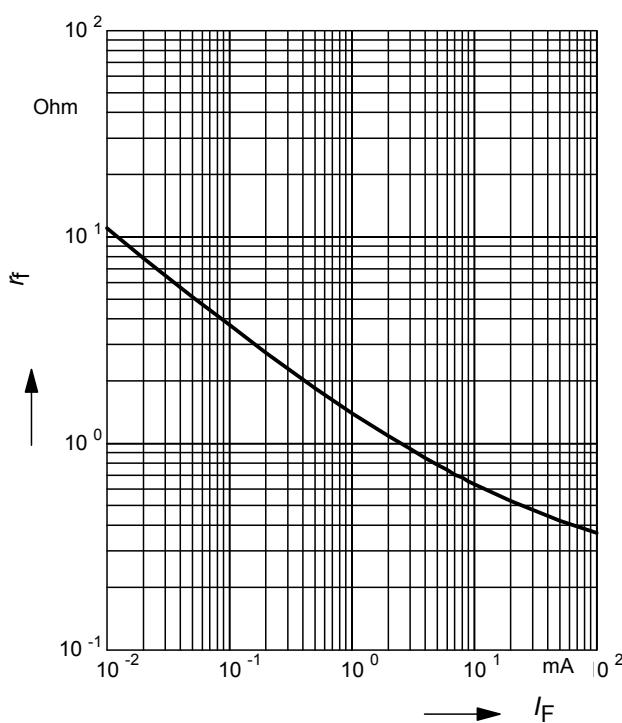
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



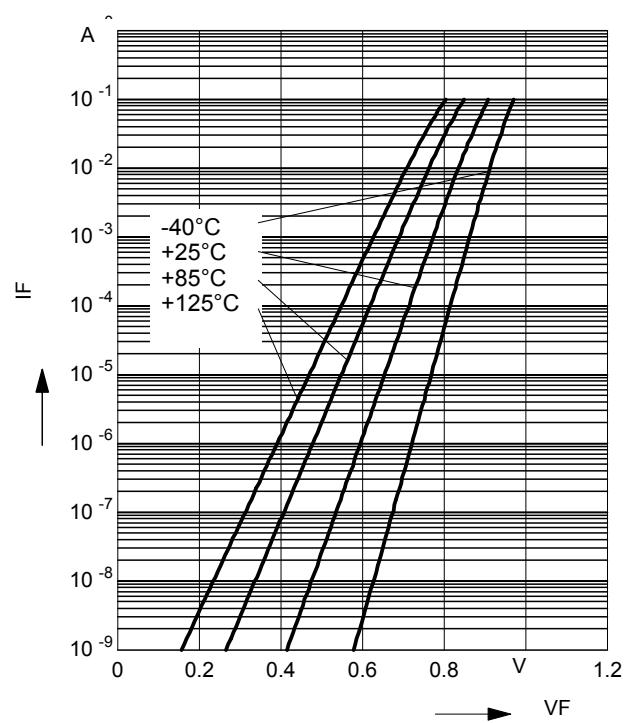
Forward resistance $r_f = f(I_F)$

$f = 100\text{MHz}$

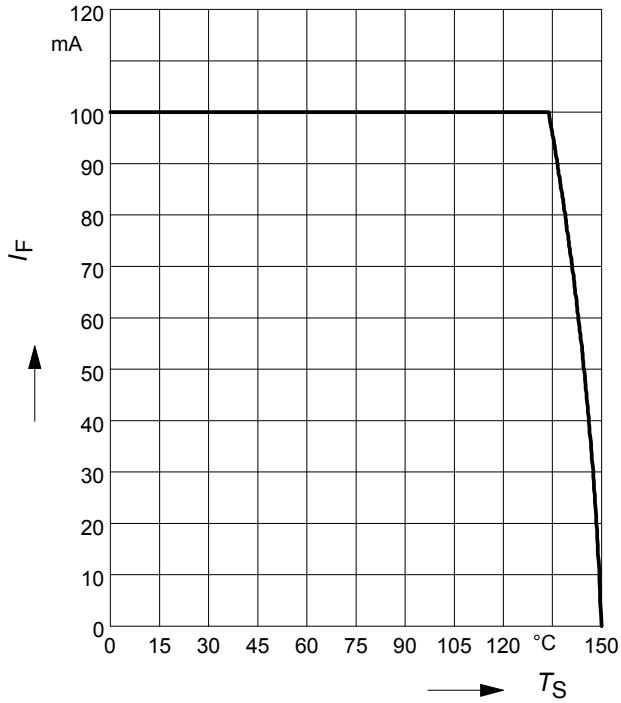


Forward current $I_F = f(V_F)$

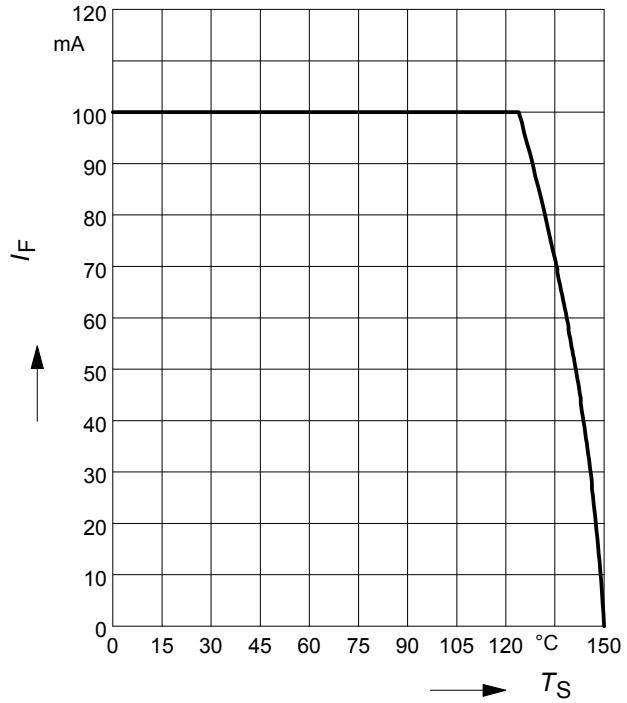
T_A = Parameter



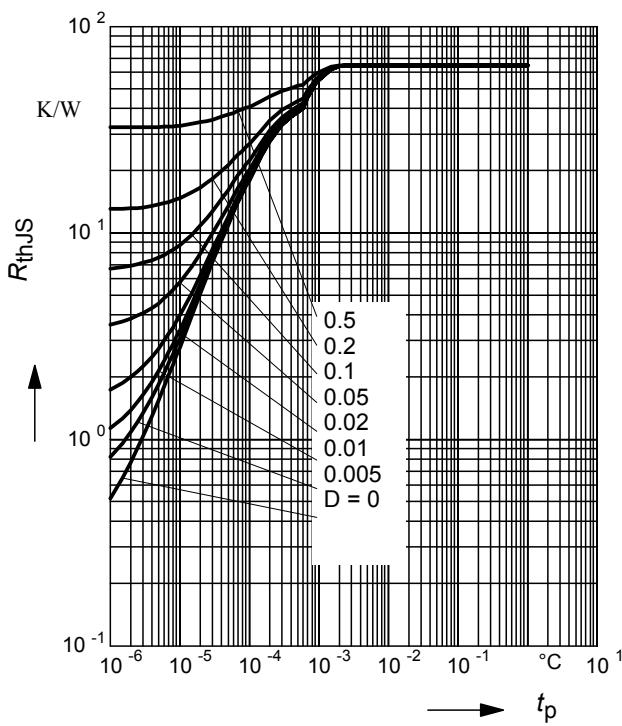
Forward current $I_F = f(T_S)$
 BAR88-02L, -07L4, -099L4



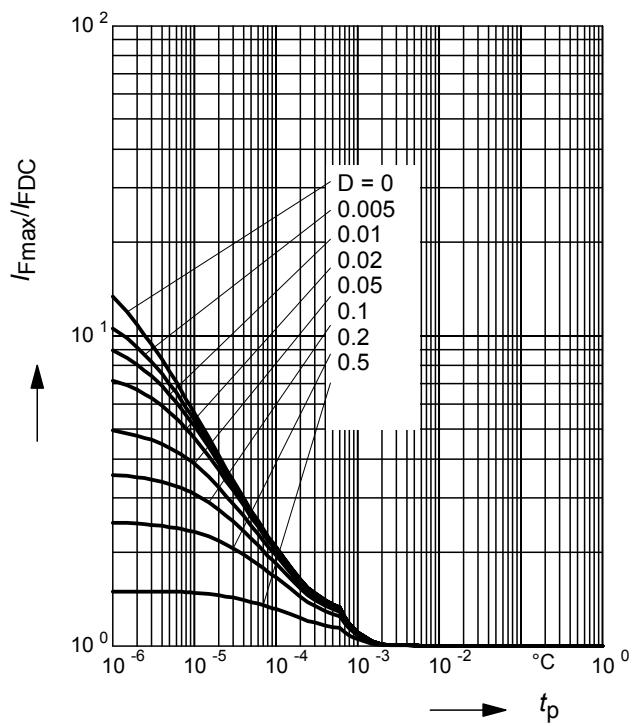
Forward current $I_F = f(T_S)$
 BAR88-02V



Permissible Puls Load $R_{thJS} = f(t_p)$
 BAR88-02L, -07L4, -099L4

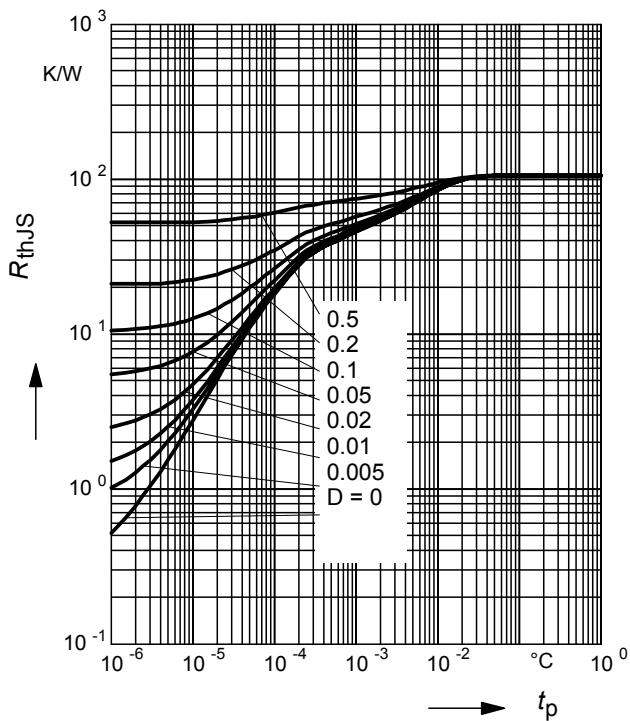


Permissible Pulse Load
 $I_{Fmax}/I_{FDC} = f(t_p)$
 BAR88-02L, -07L4, -099L4



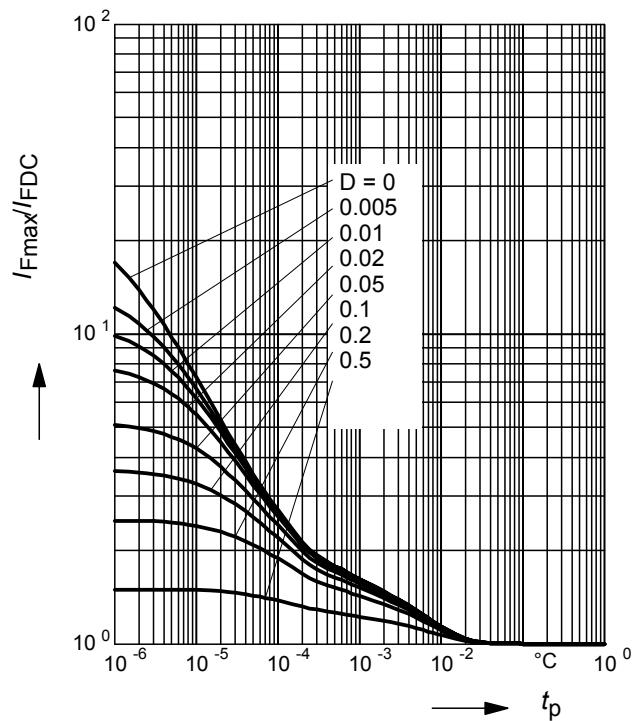
Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

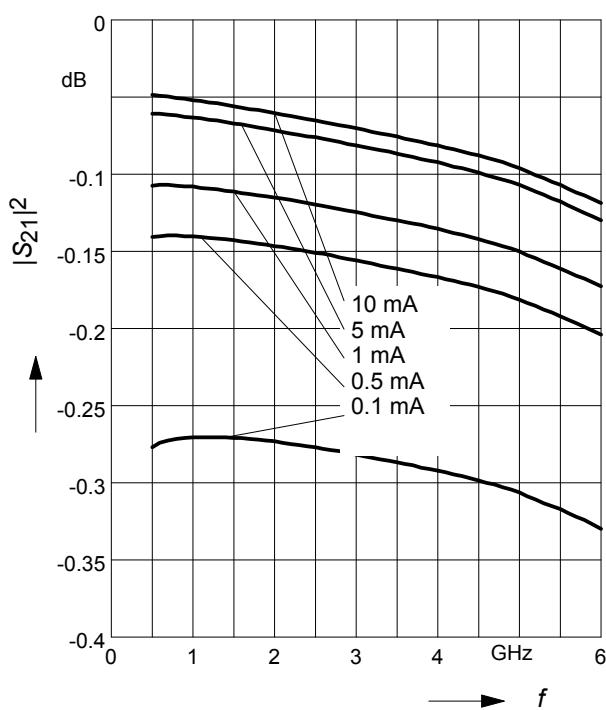
BAR88-02V


Permissible Pulse Load

$$I_{\text{Fmax}} / I_{\text{FDC}} = f(t_p)$$

BAR88-02V


Insertion loss $|S_{21}|^2 = f(f)$
 I_F = Parameter

 BAR88-02L in series configuration, $Z = 50\Omega$

Isolation $|S_{21}|^2 = f(f)$
 V_R = Parameter

 BAR88-02L in series configuration, $Z = 50\Omega$
